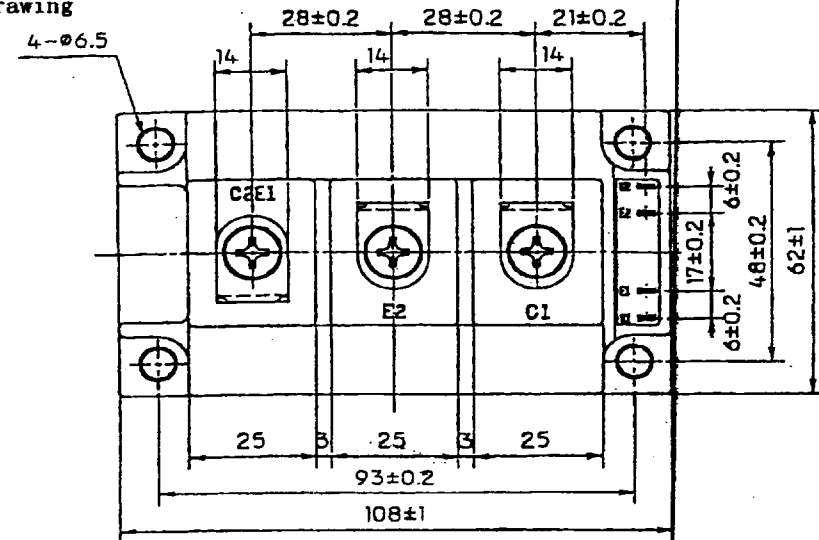


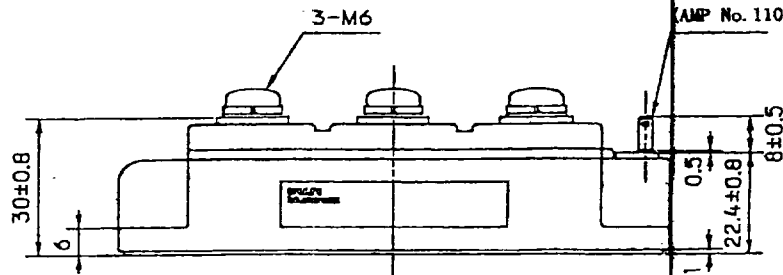
1MB I 150 SH-140 (Tentative target specification)

1. Outline Drawing

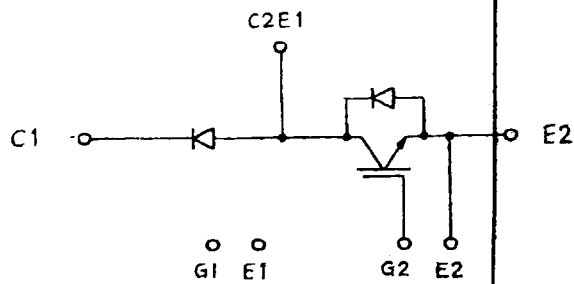
Unit : mm 4- ϕ 6.5



Tab type terminals
(AMP No. 110 equivalent)



2. Equivalent circuit



This material and the information herein is the property of Fuji Electric Co. Ltd. They shall be neither reproduced, copied, lent, or disclosed in any way whatsoever for the use of any third party nor used for the manufacturing purposes without the express written consent of Fuji Electric Co., Ltd.

	DATE	NAME	APPROVED
DRAWN	May-17-00	S. Miyashita	
CHECKED	-	-	
REVISIONS			

Fuji Electric Co., Ltd.

DWG. NO.

MT5F10879

1/2

3. Absolute Maximum Ratings (at Tc=25°C unless otherwise specified)

Items		Symbols	Ratings	Units
Collector-Emitter voltage		V _{CE}	1400	V
Gate-Emitter voltage		V _{GE}	±20	V
Collector current	Continuous	I _C (25°C/80°C)	273/185	A
	1ms	I _C pulse(25°C/80°C)	45/370	
		-I _C (25°C/80°C)	75/125	
	1ms	-I _C pulse(25°C/80°C)	45/370	
Max. power dissipation		P _C	1050	W
Operating temperature		T _j	+150	°C
Storage temperature		T _{stg}	-40~+125	°C
Isolation voltage		V _{is}	AC 2500 (1min.)	V
Screw torque	Mounting #1		3.5	N · m
	Terminals #2		4.5	

Note : *1 Recommendable value : 2.5~3.5 N · m (M5) or (M6)
 *2 Recommendable value : 3.5~4.5 N · m (M6)

4. Electrical characteristics (at Tj=25°C unless otherwise specified)

Items	Symbols	Characteristics			Conditions	Units
		min.	typ.	max.		
Zero gate voltage Collector current	I _{CE}			2.0	V _{GE} =0V, V _{CE} =1400V	mA
Gate-Emitter leakage current	I _{GE}			0.4	V _{CE} =0V, V _{GE} =±20V	μA
Gate-Emitter threshold voltage	V _{GE(th)}	5.5		8.5	V _{CE} =20V, I _C =150mA	V
Collector-Emitter saturation voltage	V _{CE(sat)}		2.3	2.7	V _{GE} =15V, I _C =150A	V
Input capacitance	C _{ies}		18000		V _{GE} =0V	pF
Output capacitance	C _{oes}		3750		V _{CE} =10V	
Reverse transfer capacitance	C _{res}		3300		f=1MHz	
Turn-on time	t _{on}		0.35	1.2	V _{CE} =600V	μs
			0.25	0.6	I _C =150A	
Turn-off time	t _{off}		0.45	1.0	V _{GE} =±15V	μs
			0.08	0.3	R _G =5.6Ω	
Diode forward on voltage	V _F		2.5	3.4	I _F =150A, V _{GE} =0V	V
Reverse recovery time	t _{rr}			0.35	I _F =150A	μs

5. Thermal resistance characteristics

Items	Symbols	Characteristics			Conditions	Units
		min.	typ.	max.		
Thermal resistance	R _{th(j-c)}		0.1	0.12	IGBT	°C/W
	R _{th(j-c)}		0.25	0.3	Diode	
	※		0.025		the base to cooling fin	
	R _{th(c-f)}					

※ This is the value which is defined mounting on the additional cooling fin with thermal compound.

This material and the information herein is the property of Fuji Electric Co., Ltd. They shall be neither reproduced, copied, lent, or disclosed in any way whatsoever for the use of any third party nor used for the manufacturing purposes without the express written consent of Fuji Electric Co., Ltd.

DATE			NAME			APPROVED			Fuj Electric Co., Ltd.		
DRAWN			CHECKED			REVISIONS					
-			-						DWG NO. MT5F10879 2/2		